



### DMN62D1LFDQ

# **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	Ι <sub>D</sub> T <sub>A</sub> = +25°C
2014	2Ω @ V <sub>GS</sub> = 4V	400mA
60V	2.5Ω @ V <sub>GS</sub> = 2.5V	350mA

This MOSFET is designed to meet the stringent requirements of

automotive applications. It is qualified to AEC-Q101, supported by a

#### N-CHANNEL ENHANCEMENT MODE MOSFET

#### Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### Mechanical Data

- Case: U-DFN1212-3 (Type C)
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)



PPAP, and is ideal for use in:

**DC-DC Converters** 

Backlighting

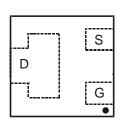


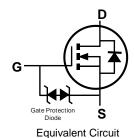


ESD PROTECTED

Top View

Bottom View





Pin-Out Top View

# Ordering Information (Note 5)

**Description and Applications** 

**Power Management Functions** 

Part Number	Compliance	Case	Packaging
DMN62D1LFDQ-7	Standard	U-DFN1212-3 (Type C)	3000/Tape & Reel
DMN62D1LFDQ-13	Standard	U-DFN1212-3 (Type C)	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, see http://www.diodes.com/products/packages.html.

## **Marking Information**

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K64	K63
YM	ҮМ
•	•

K64 = Product Type Marking Code K63 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Year	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	А	В	С	D	E	F	G	Н	I	J	К	L	М
Month	Jan	Feb	Mar	Apr	Ma	y J	un	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5		6	7	8	Q	0	N	D



# **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	60	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) $V_{GS} = 4V$	I <sub>D</sub>	400 310	mA	
Pulsed Drain Current (Note 7)		I <sub>DM</sub>	1	А

# **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 6)	PD	0.5	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 6)	R <sub>ƏJA</sub>	237	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

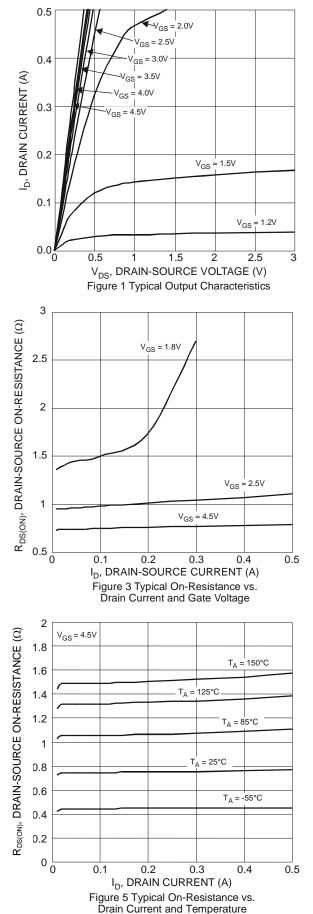
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

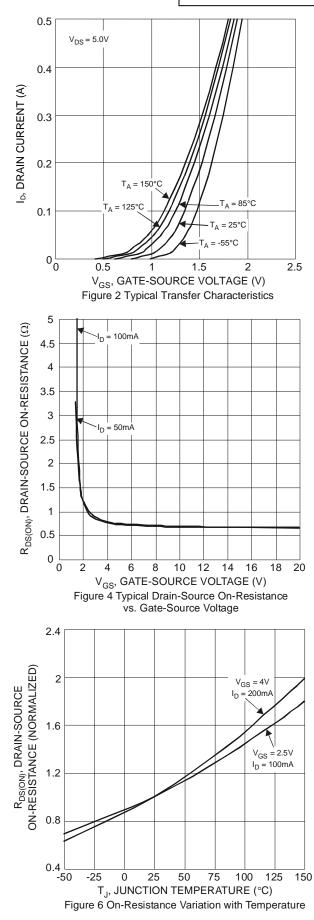
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	·					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	—	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_		1	μA	$V_{DS} = 60V, V_{GS} = 0V$
		_		±100	nA	$V_{GS} = \pm 5V, V_{DS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_		±500	nA	$V_{GS} = \pm 10V, V_{DS} = 0V$
		_	_	±2	μA	$V_{GS} = \pm 15V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.6		1	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
		_	0.8	2		$V_{GS} = 4V$ , $I_D = 100mA$
Static Drain-Source On-Resistance		—	1	2.5	Ω	$V_{GS} = 2.5V, I_D = 50mA$
	R <sub>DS(ON)</sub>	—	1.4	3	12	$V_{GS} = 1.8V, I_D = 50mA$
		—	1.8	—		$V_{GS} = 1.5V, I_D = 10mA$
Forward Transfer Admittance	Y <sub>fs</sub>	_	1.8	_	S	$V_{DS} = 10V, I_D = 200mA$
Diode Forward Voltage	V <sub>SD</sub>	_	0.8	1.3	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 9)						·
Input Capacitance	C <sub>iss</sub>	—	36	—		
Output Capacitance	Coss	—	4.6	—	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	—	3.6	—		1 - 110112
Gate Resistance	R <sub>g</sub>	_	59.8	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Qg	_	0.55	_		
Gate-Source Charge	Q <sub>gs</sub>	_	0.08	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 250mA$
Gate-Drain Charge	Q <sub>gd</sub>	_	0.12	_		$I_D = 250 \text{mA}$
Turn-On Delay Time	t <sub>D(ON)</sub>	_	2.1	_	ns	
Turn-On Rise Time	t <sub>R</sub>	_	2.8	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>		21		ns	$R_{L} = 150\Omega, R_{G} = 25\Omega,$ $I_{D} = 200 \text{mA}$
Turn-Off Fall Time	tF	_	13.9	_	ns	

 Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
Repetitive rating, pulse width limited by junction temperature.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing. Notes:



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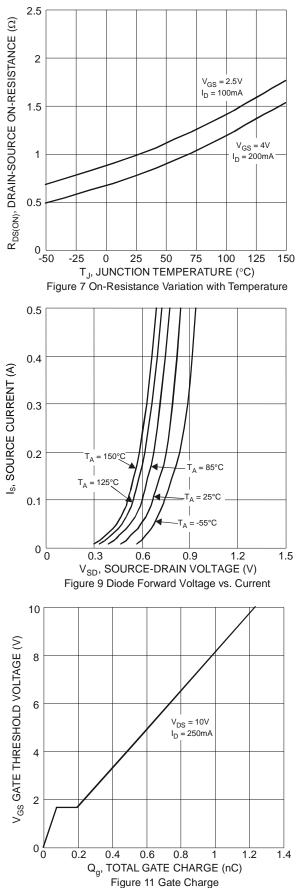


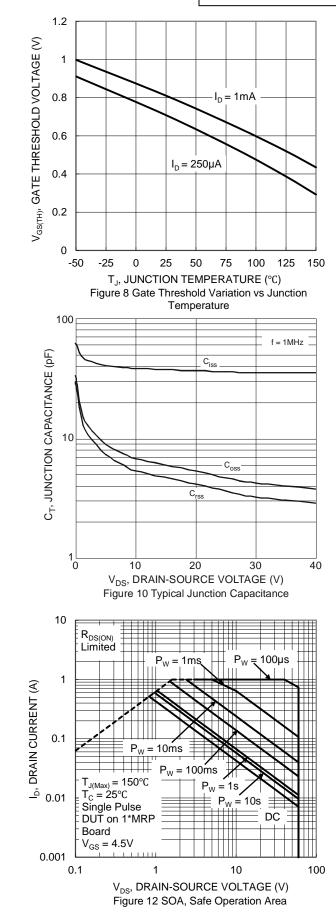


DMN62D1LFDQ Document number: DS41130 Rev. 1 - 2

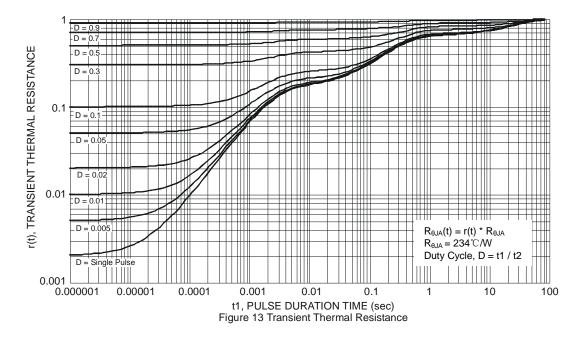


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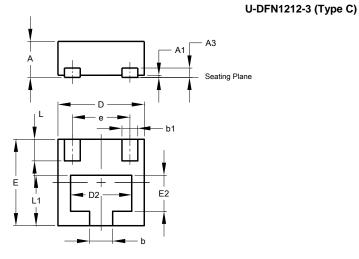






## **Package Outline Dimensions**

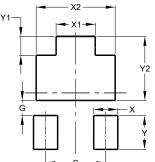
Please see http://www.diodes.com/package-outlines.html for the latest version.



U-DFN1212-3							
Туре С							
Dim	m Min Max Typ						
Α	0.47	0.53	0.50				
A1	0	0.05	0.02				
A3			0.13				
b	0.27	0.37	0.32				
b1	0.17	0.27	0.22				
D	1.15	1.25	1.20				
D2	0.75	0.95	0.85				
е	_	_	0.80				
Е	1.15	1.25	1.20				
E2	0.40	0.60	0.50				
L	0.25	0.35	0.30				
L1	0.65	0.75	0.70				
All	Dimens	sions in	mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



U-DFN1212-3 (Type C)

Dimensions	Value
Dimensions	(in mm)
С	0.800
G	0.200
Х	0.320
X1	0.520
X2	1.050
Y	0.450
Y1	0.250
Y2	0.850



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